

# **PRODUCT DATA SHEET**



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Datasheet

Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO\_questions@jgsemi.com.



TRANSISTOR (NPN)

### **FEATURES**

• Collector Current: I<sub>C</sub>=0.5A

#### SOT-523



- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

## MAXIMUM RATINGS (T<sub>A</sub>=25℃ unless otherwise noted)

| Symbol           | Parameter                     | Value   | Units      |
|------------------|-------------------------------|---------|------------|
| V <sub>CBO</sub> | Collector-Base Voltage        | 40      | V          |
| V <sub>CEO</sub> | Collector-Emitter Voltage     | 25      | V          |
| V <sub>EBO</sub> | Emitter-Base Voltage          | 5       | V          |
| Ic               | Collector Current -Continuous | 0.5     | A          |
| P <sub>C</sub>   | Collector Dissipation         | 0.2     | W          |
| Tj               | Junction Temperature          | 125     | $^{\circ}$ |
| T <sub>stg</sub> | Storage Temperature           | -55-150 | ℃          |

**ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)** 

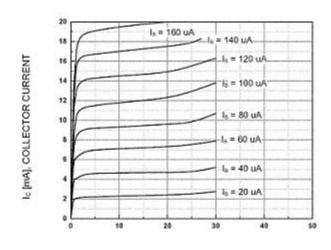
|                                      |                       |   |     |     | 1   |      |
|--------------------------------------|-----------------------|---|-----|-----|-----|------|
| Parameter                            | Symbol                | Test conditions                               | MIN | TYP | MAX | UNIT |
| Collector-base breakdown voltage     | V <sub>(BR)CBO</sub>  | I <sub>C</sub> = 100μA, I <sub>E</sub> =0     | 40  |     |     | V    |
| Collector-emitter breakdown voltage  | V <sub>(BR)CEO</sub>  | I <sub>C</sub> =1mA, I <sub>B</sub> =0        | 25  |     |     | V    |
| Emitter-base breakdown voltage       | V <sub>(BR)EBO</sub>  | I <sub>E</sub> =100μA, I <sub>C</sub> =0      | 5   |     |     | V    |
| Collector cut-off current            | Ісво                  | V <sub>CB</sub> =40 V, I <sub>E</sub> =0      |     |     | 0.1 | μA   |
| Collector cut-off current            | I <sub>CEO</sub>      | V <sub>CB</sub> =20V, I <sub>E</sub> =0       |     |     | 0.1 | μA   |
| Emitter cut-off current              | I <sub>EBO</sub>      | V <sub>EB</sub> = 5V, I <sub>C</sub> =0       |     |     | 0.1 | μA   |
|                                      | H <sub>FE(1)</sub>    | V <sub>CE</sub> =1V, I <sub>C</sub> = 50mA    | 120 |     | 400 |      |
| DC current gain                      | H <sub>FE(2)</sub>    | V <sub>CE</sub> =1V, I <sub>C</sub> = 500mA   | 50  |     |     |      |
| Collector-emitter saturation voltage | V <sub>CE</sub> (sat) | I <sub>C</sub> =500 mA, I <sub>B</sub> = 50mA |     |     | 0.6 | V    |
| Base-emitter saturation voltage      | V <sub>BE</sub> (sat) | I <sub>C</sub> =500 mA, I <sub>B</sub> = 50mA |     |     | 1.2 | V    |
| Transition frequency                 | f⊤                    | $V_{CE}=6V$ , $I_{C}=20$ mA $f=30$ MHz        | 150 |     |     | MHz  |

### CLASSIFICATION OF hfe(1)

| Rank  | L       | Н       | J       |
|-------|---------|---------|---------|
| Range | 120-200 | 200-350 | 300-400 |

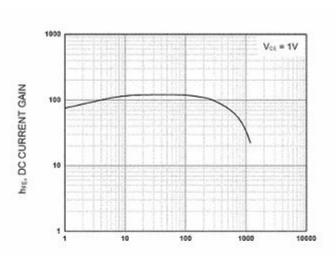


# **Typical Characteristics**



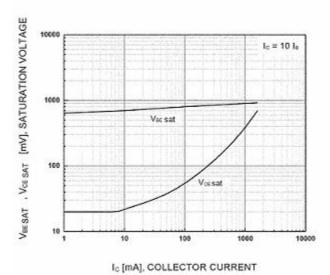


Static Characteristic

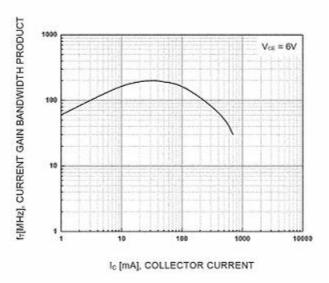


Ic [mA], COLLECTOR CURRENT

#### DC current Gain



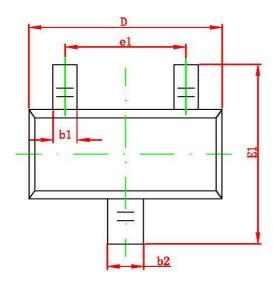
Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

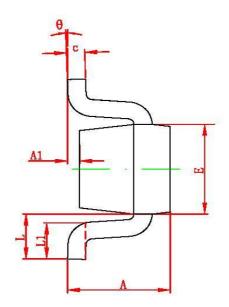


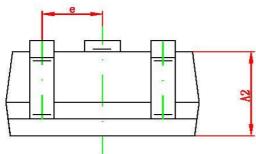
Current Gain Bandwidth Product



## SOT-523 PACKAGE OUTLINE DIMENSIONS







| Symbol | Dimensions In Millimeters |       | Dimensions In Inches |       |  |
|--------|---------------------------|-------|----------------------|-------|--|
|        | Min.                      | Max.  | Min.                 | Max.  |  |
| Α      | 0.700                     | 0.900 | 0.028                | 0.035 |  |
| A1     | 0.000                     | 0.100 | 0.000                | 0.004 |  |
| A2     | 0.700                     | 0.800 | 0.028                | 0.031 |  |
| b1     | 0.150                     | 0.250 | 0.006                | 0.010 |  |
| b2     | 0.250                     | 0.350 | 0.010                | 0.014 |  |
| С      | 0.100                     | 0.200 | 0.004                | 0.008 |  |
| D      | 1.500                     | 1.700 | 0.059                | 0.067 |  |
| Е      | 0.700                     | 0.900 | 0.028                | 0.035 |  |
| E1     | 1.450                     | 1.750 | 0.057                | 0.069 |  |
| е      | 0.500 TYP.                |       | 0.020 TYP.           |       |  |
| e1     | 0.900                     | 1.100 | 0.035                | 0.043 |  |
| L.     | 0.400 REF.                |       | 0.016 REF.           |       |  |
| L1     | 0.260                     | 0.460 | 0.010                | 0.018 |  |
| θ      | 0°                        | 8°    | 0°                   | 8°    |  |



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